## **Description**

The HFTK3420 uses advanced trench

technology to provide excellent R<sub>DS(ON)</sub>, low gate

charge and operation with gate voltages as low

as 2.5V. This device is suitable for use as a

Battery protection or in other Switching application.



**SOT-23** 

#### **General Features**

 $V_{DS} = 20V I_{D} = 6 A$ 

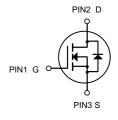
 $R_{DS(ON)}$  < 27m $\Omega$  @  $V_{GS}$ =4.5V

## **Application**

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

**Package Marking and Ordering Information** 

Product ID	Pack	Marking	Qty(PCS)
HFTK3420	SOT23	AE9T	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter		Limit	Unit	
V <sub>DS</sub>	Drain-Source Voltage		20	V	
V <sub>G</sub> s	Gate-Source Voltage		±12	V	
I <sub>D</sub>	Continuous Drain Current	T <sub>A</sub> =25℃	6	А	
		T <sub>A</sub> =70℃	3.6		
Ідм	Drain Current-Pulsed (Note 1)		15	Α	
P <sub>D</sub>	Maximum Power Dissipation		1.25	W	
T <sub>J</sub> ,T <sub>STG</sub>	Operating Junction and Storage Temperature Range		-55 To 150	$^{\circ}$	
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)		100	°C/W	



# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

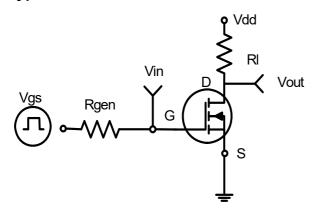
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20	22.5	-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	0.5	0.65	1.0	V
	_	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.0 A	-	22	27	mΩ
Drain-Source On-State Resistance	Rds(on)	R <sub>DS(ON)</sub> V <sub>GS</sub> =2.5V, I <sub>D</sub> =4.5A	-	28	40	mΩ
Forward Transconductance	grs	V <sub>DS</sub> =10V,I <sub>D</sub> =4A	-	10	-	S
Input Capacitance	Clss		-	500	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =8V,V <sub>GS</sub> =0V,	-	295	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	96	-	PF
Turn-on Delay Time	td(on)		-	11	-	nS
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> =10V,I <sub>D</sub> =1A	-	30	-	nS
Turn-Off Delay Time	td(off)	$V_{GS}$ =4.5V, $R_{GEN}$ =6 $\Omega$	-	35	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Qg		-	10	15	nC
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =10V,I <sub>D</sub> =3A,V <sub>GS</sub> =4.5V	-	2.3	-	nC
Gate-Drain Charge	$Q_{gd}$		-	2.9	-	nC
Diode Forward Voltage (Note 3)	VsD	V <sub>GS</sub> =0V,I <sub>S</sub> =1A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	4.5	Α

### Notes:

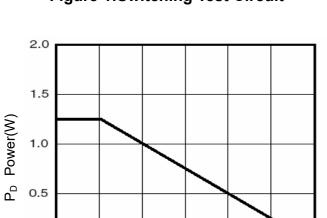
- 1. Repetitive rating: pulse width limited by maximum junction temperature.
- **2.** Surface mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse test: pulse width ≤ 300µs, duty cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



## **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 



T<sub>J</sub>-Junction Temperature(°C)

50

0.0

0

25

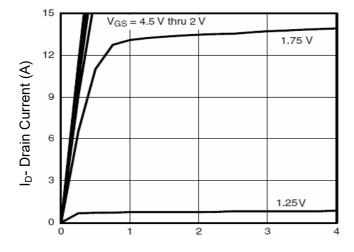
**Figure 3 Power Dissipation** 

75

100

125

150



Vds Drain-Source Voltage (V)

**Figure 5 Output Characteristics** 

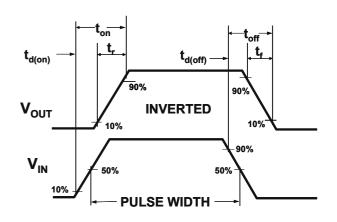


Figure 2:Switching Waveforms

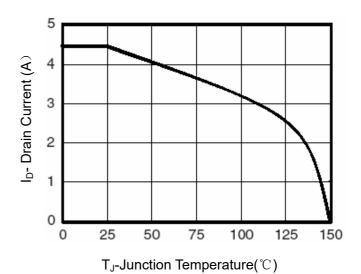


Figure 4 Drain Current

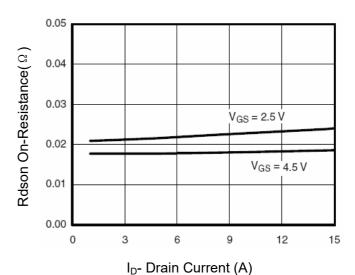


Figure 6 Drain-Source On-Resistance



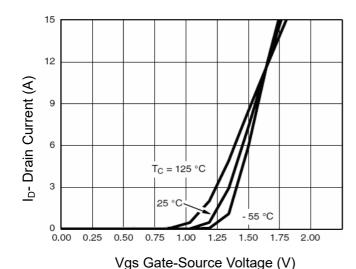
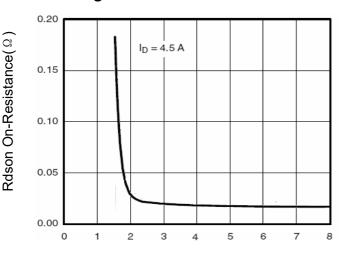


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs. Vgs

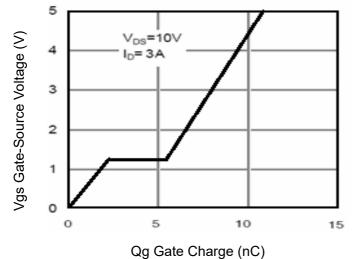


Figure 11 Gate Charge

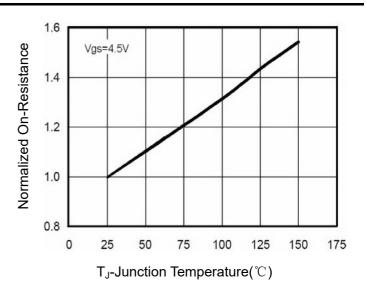


Figure 8 Drain-Source On-Resistance

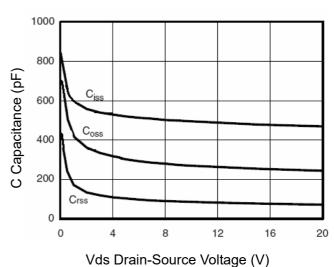


Figure 10 Capacitance vs Vds

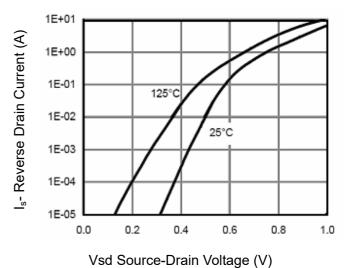
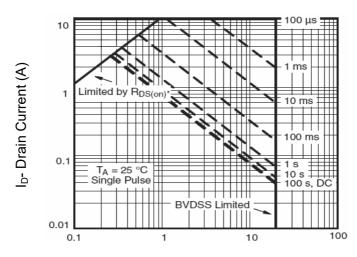


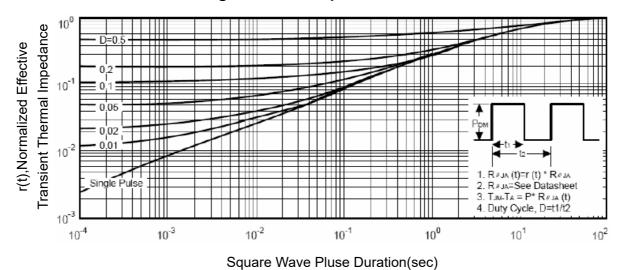
Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

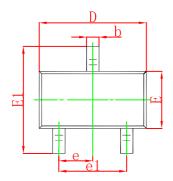
Figure 13 Safe Operation Area

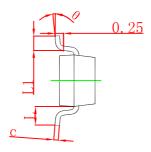


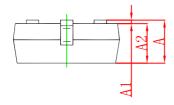
**Figure 14 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23 Package Outline Dimensions**

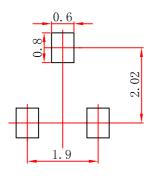






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP 0		)37 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



- Note:
  1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.

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